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Method for manufacturing semiconductor device using hydrogen annealing

Patent Assignee: SAMSUNG ELECTRONICS CO LTD (SMSU)

Inventor: LEE H S; PARK J U; PARK M H; SONG W S

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Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
KR 2001026744	A	20010406	KR 9938171	A	19990908	200233 B

Priority Applications (No Type Date): KR 9938171 A 19990908

Patent Details:

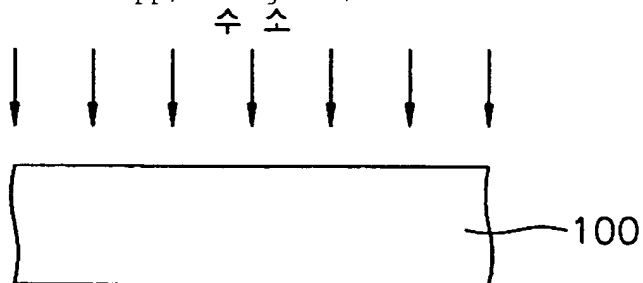
Patent No	Kind	Lan Pg	Main IPC	Filing Notes
KR 2001026744	A	1	H01L-021/324	

Abstract (Basic): KR 2001026744 A

NOVELTY - A method for manufacturing a semiconductor device using a hydrogen annealing process is provided to cure a defect in processes for forming a gate oxide layer, pad oxide layer or trench isolation, by performing the annealing process at a low temperature and within a reduce interval of time.

DETAILED DESCRIPTION - A silicon surface of a semiconductor substrate is exposed. Hydrogen is supplied to the surface of the silicon substrate and annealed in a high vacuum state from 10⁻² Torr to 10⁻⁹ Torr to cure a defect existing in the silicon surface. The annealing process is performed within a temperature scope from about 650 deg.C to 850 deg.C.

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Title Terms: METHOD; MANUFACTURE; SEMICONDUCTOR; DEVICE; HYDROGEN; ANNEAL

Derwent Class: L03; U11

International Patent Class (Main): H01L-021/324

File Segment: CPI; EPI

Manual Codes (CPI/A-N): L03-D01

Manual Codes (EPI/S-X): U11-C03J

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